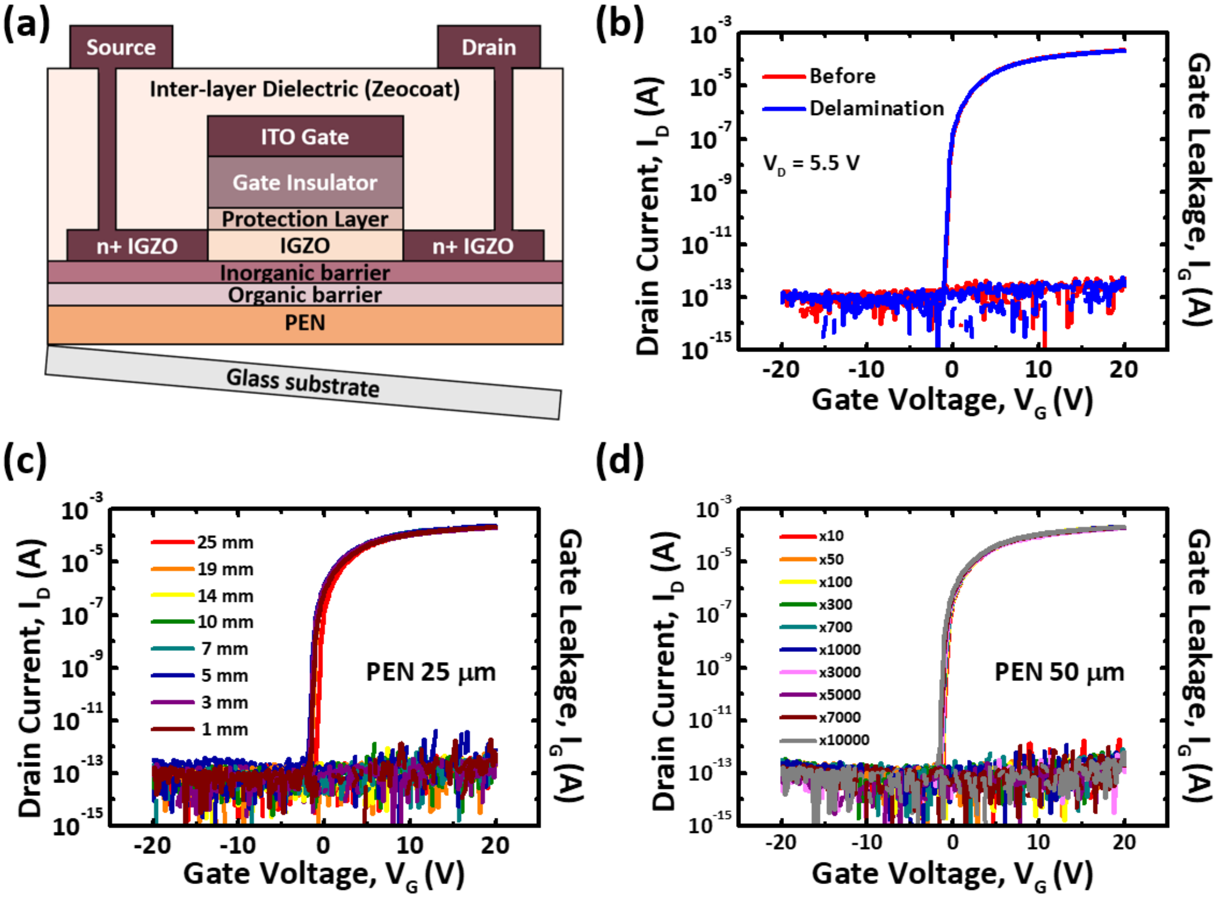

Fig. 1. (a) Schematic cross-sectional view of the fabricated flexible SA coplanar IGZO TFT. (b) I_{DS}-V_{GS} transfer characteristics of the fabricated SA coplanar IGZO TFT. (c) Variations in I_{DS}-V_{GS} transfer characteristics of the IGZO TFT fabricated on 25-µm-thick PEN substrate at various R_c from flat to 1 mm with a bending direction aligned to the channel. (d) Variations in I_{DS}-V_{GS} transfer characteristics of the IGZO TFT fabricated on 50-µm-thick PEN substrate as a function of the bending cycles at R_c of 10 mm**.**

References [1] H. E. Kim et al. IEEE Electron Device Lett., vol. 41, issue. 3, pp. 393-396 (2020).